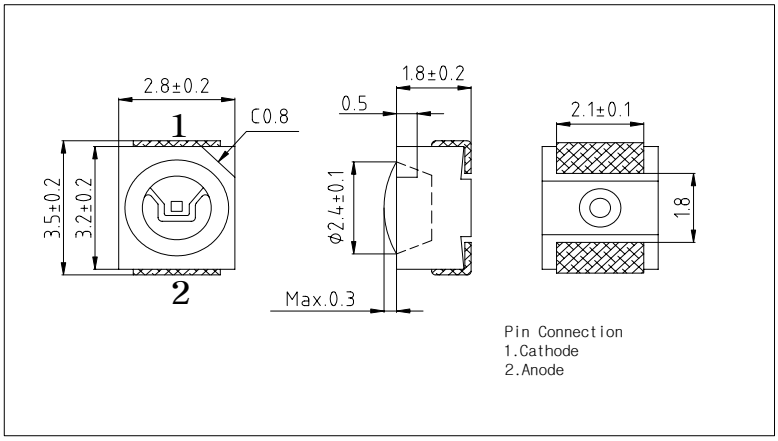
Light Emitting Diode(InGaN)

KLP-32B-X-X

KLP-32B-x-x is a high bright InGaN blue LED, and has the optimized optical characteristics.

DIMENSIONS



Features

- Transparent epoxy Encapsulent
- High Optical Output

Applications

- Display
- Indicator
- Signage

Maximum Ratings [Ta=25˚C]

Parameter	Symbol	Ratings	Unit
Reverse Voltage (w/o Zener Option)	V_R	5	V
Reverse current (w Zener Option)	I_R	50	mA
Forward current	I_F	30	mA
Pulse forward current *1	I_{FP}	0.1	A
Power dissipation	P_D	90	mW
Operating temperature	$T_{opr.}$	-30 ~ +85	°C
Storage temperature	$T_{stg.}$	-40 ~ +105	°C
Soldering Temperature *2	$T_{sol.}$	260	°C

*1. I_{FP} Measured under duty £ 1/10 @ 1KHz

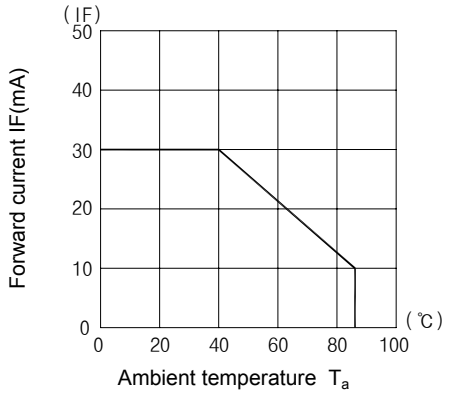
*2. Soldering time £ 5 Sec

Electro-Optical Characteristics [Ta=25˚C]

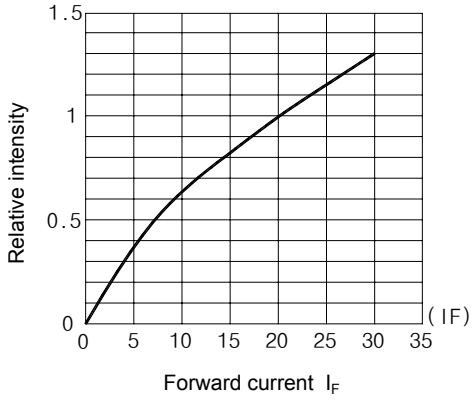
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	V_F	I_F = 20 mA	-	3.2	-	V
Optical Output Power	Po	I_F = 20 mA	9.00	12.00	-	mW
	Iv		250	350	-	mcd
Peak emission wavelength	λ_P	I_F = 20 mA	-	469	-	nm
Doninant Wave Length	λ_d	I_F = 20 mA	465	-	478	nm
Spectral half bandwidth	$\Delta\lambda$	I_F = 20 mA	-	25	-	nm
Half angle	$\Delta\Theta$	I_F = 20 mA	-	110	-	deg.

KLP-32B-X-X

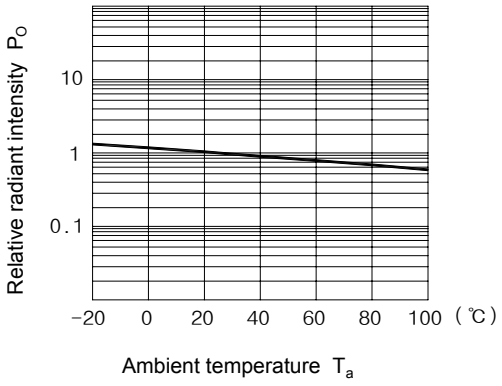
Forward current vs. Ambient temperature



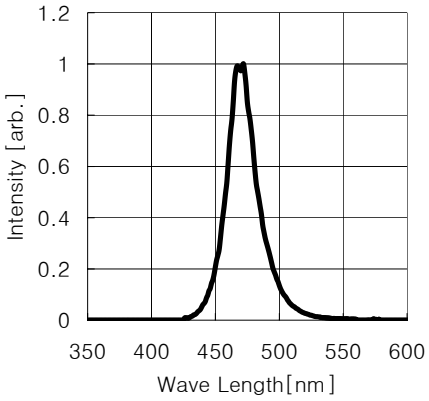
Radiant Intensity vs. Forward current



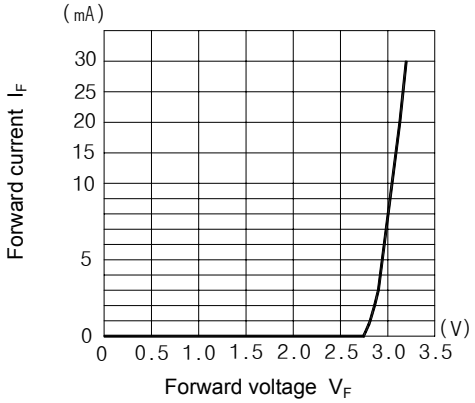
Relative radiant intensity vs. Ambient temperature



Relative intensity vs. Wavelength



Forward current vs. Forward voltage



Radiant Pattern